

SN761644

SLES252-NOVEMBER 2009

DIGITAL TV TUNER IC

Check for Samples: SN761644

FEATURES		NACE.			
 Integrated Mixer/Oscillator/PLL and IF GCA 	DBT PACKAGE (TOP VIEW)				
Mirror Pin Package of SN761640					
VHF-L, VHF-H, UHF 3-Band Local Oscillator	BS4 [] 1 ⊖ UHF RF IN1 [] 2				
RF AGC Detector Circuit		43 🗍 VLO OSC C 42 🗍 VHI OSC B			
I ² C Bus Protocol		42 1 VHI OSC C			
Bidirectional Data Transmission		40 UHF OSC B1			
High-Voltage Tuning Voltage Output	RF GND 6	39 UHF OSC C1			
 Four NPN-Type Band Switch Drivers 		38 UHF OSC C2			
One Auxiliary Port/5-Level ADC	MIX OUT1 [8	37] UHF OSC B2			
Crystal Oscillator Output		36 OSC GND			
Programmable Reference Divider Ratio		35 🛛 CP			
(24/28/32/64/80/128)					
IF GCA Enable/Disable Control	BS3 [12 BS2 [13	33 IF GND 32 AIF OUT			
Selectable digital IFOUT and Analog IFOUT	BS2 [13 BS1 [14	32 AIF OUT 31 DIF OUT1			
Standby Mode	SDA [15	30] DIF OUT2			
5-V Power Supply	SCL I 16	29 I IF GCA CTRL			
44-Pin Thin Shrink Small-Outline Package	AS [17	28 🗍 VCC			
(TSSOP)	BUS GND [18	27] IF GCA IN1			
	P5/ADC [19	26] IF GCA IN2			
APPLICATIONS	XTAL OUT 🛛 20	25 📔 IF GCA GND			
Digital TVs		24 IF GCA OUT2			
Digital CATVs	XTAL1 [22	23] IF GCA OUT1			

Set-Top Boxes

DESCRIPTION

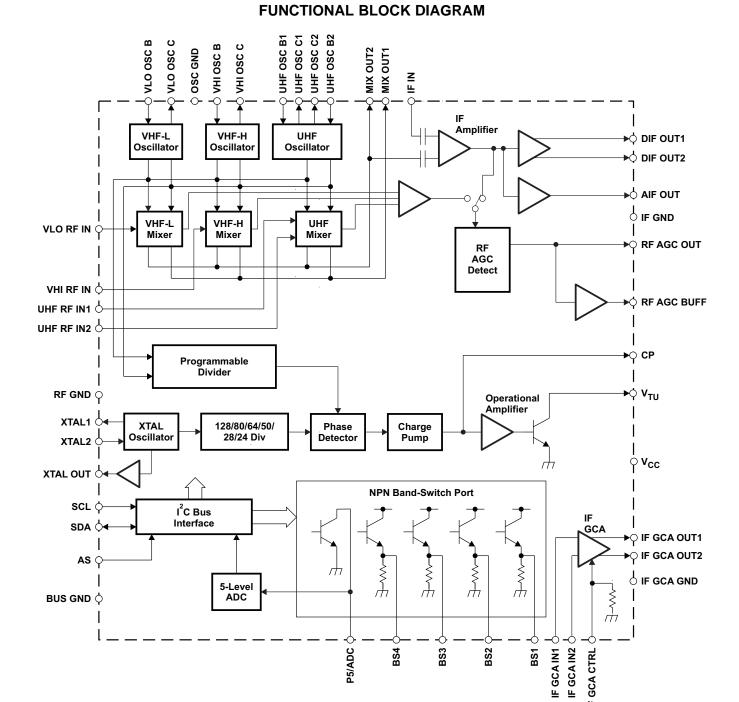
The SN761644 is a low-phase-noise synthesized tuner IC designed for digital TV tuning systems. The circuit consists of a PLL synthesizer, three-band local oscillator and mixer, RF AGC detector circuit, and IF gain-controlled amplifier. The SN761644 is available in a small-outline package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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IF GCA CTRL



TERMINAL FUNCTIONS

Table 1.

TERMINAL			
NAME	NO.	DESCRIPTION	SCHEMATIC
AIF OUT	32	IF amplifier output (analog)	Figure 8
AS	17	Address selection input	Figure 1
3S1	14	Band switch 1 output	Figure 2
BS2	13	Band switch 2 output	Figure 2
BS3	12	Band switch 3 output	Figure 2
BS4	1	Band switch 4 output	Figure 2
BUS GND	18	BUS ground	
СР	35	Charge-pump output	Figure 3
DIF OUT1	31	IF amplifier output 1	Figure 9
DIF OUT2	30	IF amplifier output 2	Figure 9
IF GCA CTRL	29	IF GCA CTRL voltage inout	Figure 4
IF GCA GND	25	IF GCA ground	3
IF GCA IN1	27	IF GCA input 1	Figure 5
IF GCA IN2	26	IF GCA input 2	Figure 5
IF GCA OUT1	23	IF GCA output 1	Figure 6
IF GCA OUT2	20	IF GCA output 2	Figure 6
IF GND	33	IF ground	
IF IN	9	IF amplifier input	Figure 7
MIXOUT1	8	Mixer output 1	Figure 10
MIXOUT2	7	Mixer output 2	Figure 10
OSC GND	36	Oscillator ground	
P5/ADC	19	Port-5 output/ADC input	Figure 11
RF AGC BUF	13	RF AGC buffer output	Figure 12
RF AGC OUT	10	RF AGC output	Figure 13
RF GND	6	RF ground	rigule 13
SCL	16		Eiguro 14
SDA	15	Serial clock input Serial data input/output	Figure 14
UHF OSC B1		UHF oscillator base 1	Figure 15
	40	UHF oscillator base 2	Figure 16 Figure 16
UHF OSC B2 UHF OSC C1	37	UHF oscillator collector 1	•
UHF OSC C1			Figure 16
	38	UHF oscillator collector 2	Figure 16
	2	UHF RF input 1	Figure 17
UHF RF IN2	3	UHF RF input 2	Figure 17
	28	Supply voltage	
VHI OSC B	42	VHF-H oscillator base	Figure 18
VHI OSC C	41	VHF-H oscillator collector	Figure 18
VHI RF IN	4	VHF-H RF input	Figure 19
VLO OSC B	44	VHF-L oscillator base	Figure 20
/LO OSC C	43	VHF-L oscillator collector	Figure 20
VLO RF IN	5	VHF-L RF input	Figure 21
VTU	34	Tuning voltage amplifier output	Figure 3
XTAL1	22	4-MHz crystal oscillator	Figure 22
XTAL2	21	4-MHz crystal oscillator	Figure 22
XTALOUT	20	4-MHz crystal oscillator buffer output	Figure 23

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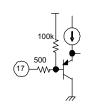


Figure 1. AS

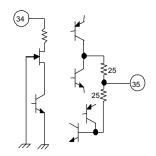


Figure 3. CP and VTU

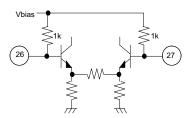


Figure 5. IF GCA IN1 and IF GCA IN2

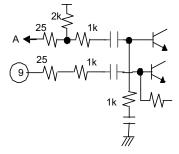


Figure 7. IF IN

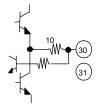


Figure 9. DIF OUT1 and DIF OUT2

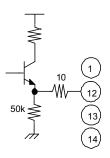


Figure 2. BS1, BS2, BS3, and BS4

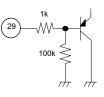


Figure 4. IF GCA CTRL

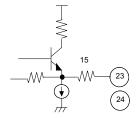


Figure 6. IF GCA OUT1 and IF GCA OUT2

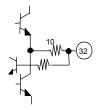


Figure 8. AIF OUT

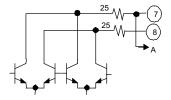
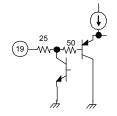


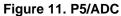
Figure 10. MIXOUT1 and MIXOUT2

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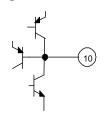


Figure 13. RF AGC OUT

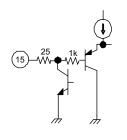


Figure 15. SDA

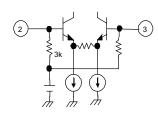


Figure 17. UHF RF IN1 and UHF RF IN2

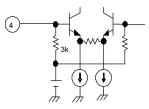


Figure 19. VHI RF IN



Figure 12. RF AGC BUF

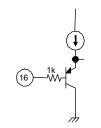


Figure 14. SCL

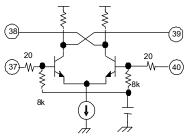


Figure 16. UHF OSC B1, UHF OSC B2, UHF OSC C1, and UHF OSC C2

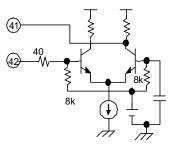


Figure 18. VHI OSC B and VHI OSC C

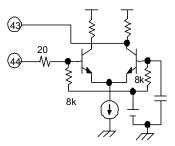
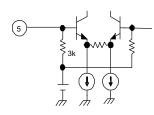


Figure 20. VLO OSC B and VLO OSC C



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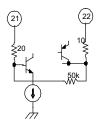
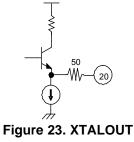


Figure 22. XTAL1 and XTAL2





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ABSOLUTE MAXIMUM RATINGS⁽¹⁾

over recommended operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range (2)	V _{CC}	-0.4	6.5	V
V_{GND}	Input voltage range 1 ⁽²⁾	RF GND, OSC GND	-0.4	0.4	V
V _{VTU}	Input voltage range 2 ⁽²⁾	VTU	-0.4	35	V
V _{IN}	Input voltage range 3 ⁽²⁾	Other pins	-0.4	6.5	V
PD	Continuous total dissipation (3)	T _A ≤ 25°C		1438	mW
T _A	Operating free-air temperature range		-20	85	°C
T _{stg}	Storage temperature range		-65	150	°C
TJ	Maximum junction temperature			150	°C
t _{SC(max)}	Maximum short-circuit time	Each pin to V _{CC} or to GND		10	S

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Voltage values are with respect to the IF GND of the circuit.

(3) Derating factor is 11.5 mW/°C for $T_A \ge 25^{\circ}C$.

RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	V _{CC}	4.5	5	5.5	V
V _{VTU}	Tuning supply voltage	VTU		30	33	V
I _{BS}	Output current of band switch	BS1 – BS4, one band switch on			10	mA
I_{P5}	Output current of port 5	P5/ADC			-5	mA
T _A	Operating free-air temperature		-20		85	°C



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric chagnes could cause the device not to meet its published specifications.

IF IN1, MIXOUT1, and MIXOUT2 (pins 7–9) withstand 1.5 kV, and all other pins withstand 2 kV, according to the Human-Body Model (1.5 k Ω , 100 pF).

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ELECTRICAL CHARACTERISTICS

Total Device and Serial Interface

 V_{CC} = 4.5 V to 5.5 V, T_A = -20°C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{CC} 1	Supply current 1	BS[1:4] = 0100, IFGCA disabled		90	120	mA
I _{CC} 2	Supply current 2	BS[1:4] = 0100, IFGCA enabled		115	145	mA
I _{CC} 3	Supply current 3	BS[1:4] = 0100, IFGCA enabled, $I_{BS} = 10 \text{ mA}$		125	155	mA
I _{CC-STBY}	Standby supply current	BS[1:4] = 1100		9		mA
VIH	High-level input voltage (SCL, SDA)		2.3			V
V _{IL}	Low-level input voltage (SCL, SDA)				1.05	V
I _{IH}	High-level input current (SCL, SDA)				10	μA
IIL	Low-level input current (SCL, SDA)		-10			μA
V _{POR}	Power-on-reset supply voltage (threshold of supply voltage between reset and operation mode)		2.1	2.8	3.5	V
I ² C Interfa	ace					
V _{ASH}	Address-select high-input voltage (AS)	$V_{CC} = 5 V$	4.5		5	V
V _{ASM1}	Address-select mid-input 1 voltage (AS)	$V_{CC} = 5 V$	2		3	V
V _{ASM2}	Address-select mid-input 2 voltage (AS)	$V_{CC} = 5 V$	1		1.5	V
V _{ASL}	Address-select low-input voltage (AS)	$V_{CC} = 5 V$			0.5	V
I _{ASH}	Address-select high-input current (AS)				50	μA
I _{ASL}	Address-select low-input current (AS)		-10			μA
V _{ADC}	ADC input voltage	See Table 11	0		V_{CC}	V
I _{ADH}	ADC high-level input current	$V_{ADC} = V_{CC}$			10	μA
I _{ADL}	ADC low-level input current	V _{ADC} = 0 V	-10			μA
V _{OL}	Low-level output voltage (SDA)	$V_{CC} = 5 \text{ V}, \text{ I}_{OL} = 3 \text{ mA}$			0.4	V
I _{SDAH}	High-level output leakage current (SDA)	V _{SDA} = 5.5 V			10	μA
f _{SCL}	Clock frequency (SCL)			100	400	kHz
t _{HD-DAT}	Data hold time	See Figure 24	0		0.9	μs
t _{BUF}	Bus free time		1.3			μs
t _{HD-STA}	Start hold time		0.6			μs
t _{LOW}	SCL-low hold time		1.3			μs
t _{HIGH}	SCL-high hold time		0.6			μs
t _{SU-STA}	Start setup time		0.6			μs
t _{SU-DAT}	Data setup time		0.1			μs
t _r	Rise time (SCL, SDA)				0.3	μs
t _f	Fall time (SCL, SDA)				0.3	μs
t _{SU-STO}	Stop setup time		0.6			μs

PLL and Band Switch

 V_{CC} = 4.5 V to 5.5 V, T_A = -20°C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
N	Divider ratio	15-bit frequency word	512		32767	
f _{XTAL}	Crystal oscillator frequency	$R_{XTAL} = 25 \ \Omega \text{ to } 300 \ \Omega$		4		MHz
Z _{XTAL}	Crystal oscillator input impedance		1.6	2.4		kΩ
V _{XLO}	XTALOUT output voltage	Load = 10 pF/5.1 k Ω , V _{CC} = 5 V, T _A = 25°C		0.48		Vр-р
V _{VTUL}	Tuning amplifier low-level output voltage	$R_{L} = 20 \text{ k}\Omega, \text{ VTU} = 30 \text{ V}$	0.2	0.3	0.46	V
IVTUOFF	Tuning amplifier leakage current	Tuning amplifier = off, VTU = 30 V			10	μA
I _{CP11}		CP[2:0] = 011		600		
I _{CP10}		CP[2:0] = 010		350		
I _{CP01}	Charge-pump current	CP[2:0] = 001		140		μA
I _{CP00}		CP[2:0] = 000		70		
I _{CP100}		CP[2:0] = 100, Mode = 1		900		
V _{CP}	Charge-pump output voltage	PLL locked		1.95		V
I _{CPOFF}	Charge-pump leakage current	$V_{CP} = 2 V, T_A = 25^{\circ}C$	-15		15	nA
I _{BS}	Band switch driver output current (BS1–BS4)				10	mA
V _{BS1}	Pond quitch driver output veltage (PS1_PS4)	I _{BS} = 10 mA	3			V
V _{BS2}	Band switch driver output voltage (BS1–BS4)	$I_{BS} = 10 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$	3.5	3.7		V
I _{BSOFF}	Band switch driver leakage current (BS1–BS4)	V _{BS} = 0 V			8	μA
I _{P5}	Band switch port sink current (P5/ADC)				-5	mA
V _{P5ON}	Band switch port output voltage (P5/ADC)	$I_{P5} = -2 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$			0.6	V

RF AGC⁽¹⁾

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 25 reference measurement circuit at 50- Ω system, IF = 44 MHz, IF filter characteristics: f_{peak} = 44 MHz (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{OAGC0}		ATC = 0		300		nA
I _{OAGC1}	RF AGCOUT output source current	ATC = 1		9		μA
I _{OAGCSINK}	RF AGCOUT peak output sink current	ATC = 0		100		μA
VOAGCH	RFAGCOUT output high voltage (max level)	ATC = 1	3.5	4	4.5	V
VOAGCL	RFAGCOUT output low voltage (min level)	ATC = 1		0.3		V
IAGCBUF	RFAGCBUF output current	ATC = 0		1.5		mA
VOAGCBFH	RFAGCBUF output high voltage (max level)	ATC = 1	3.5	4	4.5	V
VOAGCBFL	RFAGCBUF output low voltage (min level)	ATC = 1		0.3		V
V _{AGCSP00}		ATP[2:0] = 000		114		
V _{AGCSP01}		ATP[2:0] = 001		112		
V _{AGCSP02}		ATP[2:0] = 010		110		
V _{AGCSP03}	Start-point IF output level	ATP[2:0] = 011		108		dBµV
V _{AGCSP04}		ATP[2:0] = 100		106		
V _{AGCSP05}		ATP[2:0] = 101		104		
V _{AGCSP06}		ATP[2:0] = 110		102		

(1) When AISL=1, RF AGC function is not available at VHF-L band (output level is undefined).



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Mixer, Oscillator, IF Amplifier (DIF OUT)

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 25 reference measurement circuit at 50- Ω system, IF = 44 MHz, IF filter characteristics: f_{peak} = 44 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYP	UNIT
G _{C1D}		$f_{in} = 57 \text{ MHz}^{(1)}$	35	
G _{C3D}	Conversion gain (mixer-IF amplifier), VHF-LOW	f _{in} = 171 MHz ⁽¹⁾	35	dB
G _{C4D}		$f_{in} = 177 \text{ MHz}^{(1)}$	35	
G _{C6D}	Conversion gain (mixer-IF amplifier), VHF-HIGH	$f_{in} = 467 \text{ MHz}^{(1)}$	35	dB
G _{C7D}		$f_{in} = 473 \text{ MHz}^{(1)}$	35	٩D
G _{C9D}	Conversion gain (mixer-IF amplifier), UHF	$f_{in} = 864 \text{ MHz}^{(1)}$	35	dB
NF _{1D}	Noise figure, VHF-LOW	f _{in} = 57 MHz	9	dB
NF _{3D}	Noise ligule, VHF-LOW	f _{in} = 171 MHz	9	uБ
NF _{4D}	Noise figure, VHF-HIGH	f _{in} = 177 MHz	9	dB
NF _{6D}		f _{in} = 467 MHz	10	uБ
NF _{7D}	Noise figure, UHF	f _{in} = 473 MHz	10	dB
NF _{9D}		f _{in} = 864 MHz	12	uБ
CM _{1D}	Input voltage causing 1% cross-modulation distortion,	$f_{in} = 57 \text{ MHz}^{(2)}$	79	dBµV
CM _{3D}	VHF-LOW	$f_{in} = 171 \text{ MHz}^{(2)}$	79	иБμν
CM _{4D}	Input voltage causing 1% cross-modulation distortion,	f _{in} = 177 MHz ⁽²⁾	79	ا ۱۳۰۹
CM _{6D}	VHF-HIGH	f _{in} = 467 MHz ⁽²⁾	79	dBµV
CM _{7D}	Input voltage causing 1% cross-modulation distortion, UHF	f _{in} = 473 MHz ⁽²⁾	77	dBµV
CM _{9D}	Input voltage causing 1% closs-modulation distortion, one	$f_{in} = 864 \text{ MHz}^{(2)}$	77	иБμν
V _{IFO1D}	IF output voltage, VHF-LOW	f _{in} = 57 MHz	117	dBµV
V _{IFO3D}	ir ouiput voitage, vrii -LOW	f _{in} = 171 MHz	117	υвμν
V _{IFO4D}	IF output voltage, VHF-HIGH	f _{in} = 177 MHz	117	dBµV
V _{IFO6D}	ir ouiput voitage, vrii -riigir	f _{in} = 467 MHz	117	υвμν
V _{IFO7D}	IF output voltage, UHF	f _{in} = 473 MHz	117	dBµV
V _{IFO9D}	ir ouput voltage, or in	f _{in} = 864 MHz	117	υвμν
Φ _{PLVL1D}	Phase noise, VHF-LOW	$f_{in} = 57 \text{ MHz}^{(3)}$	-90	dBc/Hz
Φ _{PLVL3D}		$f_{in} = 171 \text{ MHz}^{(4)}$	-85	
Φ_{PLVL4D}	Phase noise, VHF-HIGH	f _{in} = 177 MHz ⁽³⁾	-85	dBc/Hz
Φ_{PLVL6D}		$f_{in} = 467 \text{ MHz}^{(4)}$	-77	
Φ _{PLVL7D}	Phase noise, UHF	$f_{in} = 473 \text{ MHz}^{(3)}$	-80	dBc/Hz
Φ _{PLVL9D}	רומש ווטושל, טרור	f _{in} = 864 MHz ⁽⁴⁾	-77	UDU/HZ

 $\begin{array}{ll} \text{(1)} & \text{IF} = 44 \; \text{MHz}, \, \text{RF} \; \text{input level} = 70 \; \text{dB}\mu\text{V}, \, \text{differential output} \\ \text{(2)} & f_{\text{undes}} = f_{\text{des}} \pm 6 \; \text{MHz}, \, \text{Pin} = 70 \; \text{dB}\mu\text{V}, \, \text{AM} \; 1 \; \text{kHz}, \; 30\%, \, \text{DES/CM} = \text{S/I} = 46 \; \text{dB} \\ \text{(3)} & \text{Offset} = 1 \; \text{kHz}, \, \text{CP} \; \text{current} = 350 \; \mu\text{A}, \, \text{reference divider} = 64 \\ \end{array}$

(4) Offset = 1 kHz, CP current = 900 µA, reference divider = 64



Mixer, Oscillator, IF Amplifier (AIF OUT)

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 25 reference measurement circuit at 50- Ω system, IF = 45.75 MHz, IF filter characteristics: f_{peak} = 44 MHz (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TYP	UNIT
G _{C1A}		f _{in} = 55.25 MHz ⁽¹⁾	29	
G _{C3A}	Conversion gain (mixer-IF amplifier), VHF-LOW	f _{in} = 169.25 MHz ⁽¹⁾	29	dB
G _{C4A}		f _{in} = 175.25 MHz ⁽¹⁾	29	
G _{C6A}	Conversion gain (mixer-IF amplifier), VHF-HIGH	f _{in} = 465.25 MHz ⁽¹⁾	29	dB
G _{C7A}		$f_{in} = 471.25 \text{ MHz}^{(1)}$	29	
G _{C9A}	Conversion gain (mixer-IF amplifier), UHF	f _{in} = 862.25 MHz ⁽¹⁾	29	dB
NF _{1A}		f _{in} = 55.25 MHz	9	
NF _{3A}	Noise figure, VHF-LOW	f _{in} = 169.25 MHz	9	dB
NF _{4A}		f _{in} = 175.25 MHz	9	dB
NF _{6A}	Noise figure, VHF-HIGH	f _{in} = 465.25 MHz	10	uв
NF _{7A}		f _{in} = 471.25 MHz	10	
NF _{9A}	Noise figure, UHF	f _{in} = 862.25 MHz	12	dB
CM _{1A}	Input voltage causing 1% cross-modulation distortion,	f _{in} = 55.25 MHz ⁽²⁾	79	/ ۱۰۰۹
CM _{3A}	VHF-LOW	f _{in} = 169.25 MHz ⁽²⁾	79	dBµV
CM _{4A}	Input voltage causing 1% cross-modulation distortion,	f _{in} = 175.25 MHz ⁽²⁾	79	/ ۱۰۰ طه
CM _{6A}	VHF-HIGH	f _{in} = 465.25 MHz ⁽²⁾	79	dBµV
CM _{7A}	Input voltage equains 10/ errors modulation distortion LILIE	f _{in} = 471.25 MHz ⁽²⁾	79	/ ۱۰۰۹
CM _{9A}	Input voltage causing 1% cross-modulation distortion, UHF	f _{in} = 862.25 MHz ⁽²⁾	77	dBµV
/IFO1A	IF output voltage, VHF-LOW	f _{in} = 55.25 MHz	117	dBµV
/ _{IFO3A}		f _{in} = 169.25 MHz	117	ивμν
/ _{IFO4A}	IF output voltage, VHF-HIGH	f _{in} = 175.25 MHz	117	dBµV
/ _{IFO6A}	ir ouiput voltage, vin-nign	f _{in} = 465.25 MHz	117	ивμν
/ _{IFO7A}	IF output voltage, UHF	f _{in} = 471.25 MHz	117	dBµV
/ _{IFO9A}	IF oulput voltage, OHF	f _{in} = 862.25 MHz	117	uвµv
Þ _{PLVL1A}		f _{in} = 55.25 MHz ⁽³⁾	-95	dBc/Hz
PLVL3A	Phase noise, VHF-LOW	f _{in} = 169.25 MHz ⁽³⁾	-95	UDC/H
Þ _{PLVL4A}		f _{in} = 175.25 MHz ⁽³⁾	-90	dBc/Hz
PLVL6A	Phase noise, VHF-HIGH	f _{in} = 465.25 MHz ⁽³⁾	-90	aBC/H
Þ _{PLVL7A}		f _{in} = 471.25 MHz ⁽³⁾	-85	dD a/L
⊅ _{PLVL9A}	Phase noise, UHF	f _{in} = 862.25 MHz ⁽³⁾	-90	dBc/Hz

 $\begin{array}{ll} \text{(1)} & \text{IF} = 44 \; \text{MHz}, \, \text{RF} \; \text{input level} = 70 \; \text{dB}\mu\text{V} \\ \text{(2)} & f_{\text{undes}} = f_{\text{des}} \pm 6 \; \text{MHz}, \, \text{Pin} = 70 \; \text{dB}\mu\text{V}, \, \text{AM} \; 1 \; \text{kHz}, \; 30\%, \, \text{DES/CM} = \text{S/I} = 46 \; \text{dB} \\ \text{(3)} & \text{Offset} = 10 \; \text{kHz}, \; \text{CP} \; \text{current} = 70 \; \mu\text{A}, \, \text{reference divider} = 128 \\ \end{array}$



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IF Gain Controlled Amplifier

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 25 reference measurement circuit at 50- Ω system, IF = 44 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{IFGCA}	Input current (IF GCA CTRL)	V _{IFGCA} = 3 V		30	60	μA
VIFGCAMAX	Maximum gain control voltage	Gain maximum	3		V _{CC}	V
VIFGCAMIN	Minimum gain control voltage	Gain minimum	0		0.2	V
GIFGCAMAX	Maximum gain	V _{IFGCA} = 3 V		65		dB
GIFGCAMIN	Minimum gain	V _{IFGCA} = 0 V		-1		dB
GCRIFGCA	Gain control range	$V_{IFGCA} = 0 V \text{ to } 3 V$		66		dB
VIFGCAOUT	Output voltage	Single-ended output, V _{IFGCA} = 3 V		2.1		Vp-p
NFIFGCA	Noise figure	V _{IFGCA} = 3 V		11		dB
IM3 _{IFGCA}	Third order intermodulation distortion			-50		dBc
IIP _{3IFGCA}	Input intercept point	V _{IFGCA} = 0 V		11		dBm
RIFGCAIN	Input resistance (IF GCA IN1, IF GCA IN2)			1		kΩ
RIFGCAOUT	Output resistance (IF GCA OUT1, IF GCA OUT2)			25		Ω



FUNCTIONAL DESCRIPTION

I²C Bus Mode

I^2C Write Mode (R/W = 0)

[1		1			
	MSB							LSB	
Address byte (ADB)	1	1	0	0	0	MA1	MA0	$R/\overline{W} = 0$	A ⁽¹⁾
Divider byte 1 (DB1)	0	N14	N13	N12	N11	N10	N9	N8	A ⁽¹⁾
Divider byte 2 (DB2)	N7	N6	N5	N4	N3	N2	N1	N0	A ⁽¹⁾
Control byte 1 (CB1)	1	0	ATP2	ATP1	ATP0	RS2	RS1	RS0	A ⁽¹⁾
Band switch byte (BB)	CP1	CP0	AISL	P5	BS4	BS3	BS2	BS1	A ⁽¹⁾
Control byte 2 (CB2)	1	1	ATC	MODE	T3/DISGCA	T2/IFDA	T1/CP2	T0/XLO	A ⁽¹⁾

Table 2. Write Data Format

(1) A : acknowledge

Table 3. Write Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
MA[1:0]	Address-set bits (see Table 4)	
N[14:0]	Programmable counter set bits	N14 = N13 = N12 = = N0 = 0
	$N = N14 \times 2^{14} + N13 \times 2^{13} + + N1 \times 2 + N0$	
ATP[2:0]	RF AGC start-point control bits (see Table 5)	ATP[2:0] = 000
RS[2:0]	Reference divider ratio-selection bits (see Table 6)	RS[2:0] = 000
CP[1:0]	Charge-pump current-set bit (see Table 7)	CP[1:0] = 00
AISL ⁽¹⁾	RF AGC detector input selection bit	AISL = 0
	AISL = 0: IF amplifier AISL = 1: Mixer output	
P5	Port output/ADC input control bit	P5 = 0
	P5 = 0: ADC INPUT P5 = 1: Tr = ON	
BS[4:1]	Band switch control bits	BSn = 0
	BSn = 0: Tr = OFF BSn = 1: Tr = ON	
	Band selection by BS[1:2]	
	BS1 BS2	
	1 0 VHF-LO 0 1 VHF-HI 0 0 UHF 1 1 Standby mode/stop MOP function (XTALOUT is available in standby mode)	
ATC	RF AGC current-set bit	ATC = 0
	ATC = 0: Current = 300 nA ATC = 1: Current = 9 μA	
Mode T3/DISGCA T2/IFDA	Mode IFGCA enabled, DIFOUT1, 2 selected = 0 : T3/DISGCA, T2/IFDA, T1/CP2, T0/XLO are Test bits and XTALOUT control bit (see Table 8)	MODE = 0 T[3:0] = 0000
T1/CP2 T0/XLO	Mode T3/DISGCA = 0 : IF GCA enabled = 1 T3/DISGCA = 1 : IF GCA disabled T2/IFDA = 0 : DIFOUT1, 2 selected T2/IFDA = 1 : AIFOUT selected T1/CP2 : lcp control bit, See Table 7 T0/XLO = 0 : XTALOUT enabled T0/XLO = 1 : XTALOUT disabled	

(1) When AISL = 1, RF AGC function is not available at VHF-L band (Output level is undefined.)



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MA1	MA1 MA0 VOLTAGE APPLIED ON AS INPU							
0	0	0 V to 0.1 V _{CC} (Low)						
0	1	OPEN, or 0.2 V_{CC} to 0.3 V_{CC} (Mid2)						
1	0	0.4 V_{CC} to 0.6 V_{CC} (Mid1)						
1	1	0.9 V_{CC} to V_{CC} (High)						

Table 4. Address Selection

Table 5. RF AGC Start Point⁽¹⁾

ATP2	ATP1	ATP0	IFOUT LEVEL (dBµV)
0	0	0	114
0	0	1	112
0	1	0	110
0	1	1	108
1	0	0	106
1	0	1	104
1	1	0	102
1	1	1	Disabled

(1) When AISL=1, RF AGC function is not available at VHF-L band (output level is undefined).

Table 6. Reference Divider Ratio

RS2	RS1	RS0	REFERENCE DIVIDER RATIO
0	0	0	24
0	0	1	28
0	1	0	32
0	1	1	64
1	0	0	128
1	Х	1	80

Table 7. Charge-Pump Current

C 1									
MODE	CP2	CP1	CP0	CHARGE PUMP CURRENT (µA)					
Х	0	0	0	70					
Х	0	0	1	140					
Х	0	1	0	350					
Х	0	1	1	600					
1	1	0	0	900					

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Table 8. Test Bits/XTALOUT Co	ontrol ⁽¹⁾
-------------------------------	-----------------------

MODE	T3/DISGCA	T2/IFDA	T1/CP2	T0/XLO	DEVICE OPERATION	XTALOUT 4-MHz OUTPUT
0	0	0	0	0	Normal operation	Enabled
0	0	0	0	1	Normal operation	Disabled
1	Х	Х	Х	0	Normal operation	Enabled
1	Х	Х	Х	1	Normal operation	Disabled
0	Х	1	Х	Х	Test mode	Not available
0	1	Х	Х	Х	Test mode	Not available

(1) RFAGC and XTALOUT are not available in test mode.

I^2C Read Mode (R/W = 1)

Table 9. Read Data Format

	MSB							LSB	
Address byte (ADB)	1	1	0	0	0	MA1	MA0	$R/\overline{W} = 1$	A ⁽¹⁾
Status byte (SB)	POR	FL	1	1	Х	A2	A1	A0	-

(1) A : acknowledge

Table 10. Read Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
MA[1:0]	Address-set bits (see Table 4)	
POR	Power-on reset flag	POR = 1
	POR set: power on	
	POR reset: end-of-data transmission procedure	
FL ⁽¹⁾	In-lock flag	
	PLL locked (FL=1), Unlocked (FL=0)	
A[2:0]	Digital data of ADC (see Table 11)	
	Bit P5 must be set to 0.	

(1) Lock detector works by using phase error pulse at the phase detector. Lock flag (FL) is set or reset according to this pulse width disciminator. Hence unstableness of PLL may cause the lock detect circuit to malfunction. In order to stable PLL, it is required to evaluate application circuit in various condition of loop-gain (loo-p filter, CP current), and to verify with whole conditions of actual application.

A2	A1	A0	VOLTAGE APPLIED ON ADC INPUT
1	0	0	0.6 V_{CC} to V_{CC}
0	1	1	0.45 V_{CC} to 0.6 V_{CC}
0	1	0	0.3 V_{CC} to 0.45 V_{CC}
0	0	1	0.15 V_{CC} to 0.3 V_{CC}
0	0	0	0 to 0.15 V _{CC}

Table 11. Address Selection⁽¹⁾

(1) Accuracy is 0.03 x V_{CC} .



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Example I²C Data Write Sequences

Telegram examples:

Start-ADB-DB1-DB2-CB1-BB-CB2-Stop Start-ADB-DB1-DB2-Stop Start-ADB-CB1-BB-CB2-Stop Start-ADB-CB1-BB-Stop Start-ADB-CB2-Stop

Abbreviations:

ADB: Address byte BB: Band switch byte CB1: Control byte 1 CB2: Control byte 2 DB1: Divider byte 1 DB2: Divider byte 2 Start: Start condition Stop: Stop condition

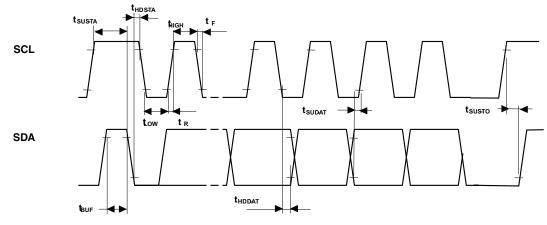
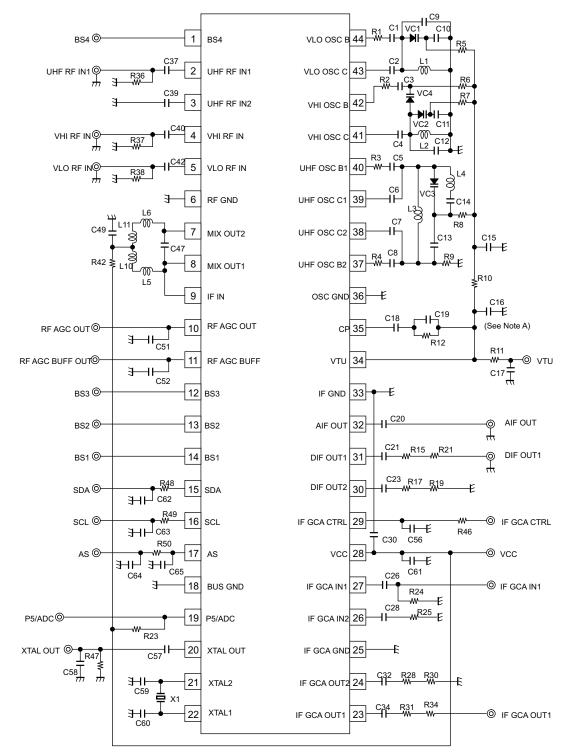


Figure 24. I²C Timing Chart



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APPLICATION INFORMATION



- To prevent abnormal oscillation, connect C16, which does not affect a PLL. Α.
- В. This application information is advisory and performance-check is required at actual application circuits. TI assumes no responsibility for the consequences of use of this circuit, such as an infringement of intellectual property rights or other rights, including patents, of third parties.

Figure 25. Reference Measurement Circuit



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Table 12. Component Values for Measurement Circuit⁽¹⁾

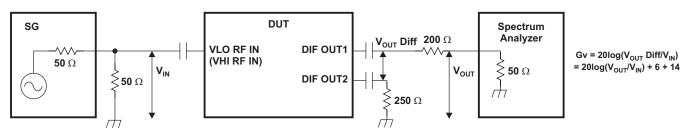
PARTS NAME	VALUE	PARTS NAME	VALUE		
C1 (VLO OSC B)	1 pF	L1 (VLO OSC)	3.0 mm, 7T, wire 0.32 mm		
C2 (VLO OSC C)	2 pF	L2 (VHI OSC)	2.0 mm, 3T, wire 0.4 mm		
C3 (VHI OSC B)	7 pF	L3 (UHF OSC)	1.8 mm, 3T, wire 0.4 mm		
C4 (VHI OSC C)	5 pF	L4 (UHF OSC)	1.8 mm, 3T, wire 0.4 mm		
C5 (UHF OSCB1)	1.5 pF	L5 (MIX OUT)	680 nH (LK1608R68K-T)		
C6 (UHF OSCC1)	1 pF	L6 (MIX OUT)	680 nH (LK1608R68K-T)		
C7 (UHF OSCC2)	1 pF	L10 (MIX OUT)	Short		
C8 (UHF OSCB2)	1.5 pF	L11 (MIX OUT)	Short		
C9 (VLO OSC)	OPEN	R1(VLO OSC B)	0		
C10(VLO OSC)	43 pF	R2 (VHI OSC B)	4.7 Ω		
C11 (VHI OSC)	51 pF	R3 (UHF OSC B1)	4.7 Ω		
C12 (VHI OSC)	0.5 pF	R4 (UHF OSC B2)	0		
C13 (UHF OSC)	10 pF	R5 (VLO OSC)	3.3 kΩ		
C14 (UHF OSC)	100 pF	R6 (VHI OSC)	3.3 kΩ		
C15 (VTU)	2.2 nF/50 V	R7 (VHI OSC)	3.3 kΩ		
C16 (CP)	150 pF/50 V	R8 (UHF OSC)	1 kΩ		
C17 (VTU)	2.2 nF/50 V	R9 (UHF OSC)	2.2 k		
C18(CP)	0.01 u/50 V	R10 (VTU)	3 kΩ		
C19(CP)	22 pF/50 V	R11 (VTU)	20 kΩ		
C20 (AIF OUT)	2.2 nF	R12 (CP)	47 kΩ		
C21 (DIF OUT1)	2.2 nF	R15 (DIF OUT1)	200 Ω		
C23 (DIF OUT2)	2.2 nF	R17 (DIF OUT2)	200 Ω		
C26 (IF GCA IN1)	2.2 nF	R19 (DIF OUT2)	50 Ω		
C28 (IF GCA IN2)	2.2 nF	R21 (DIF OUT1)	0		
C30 (VCC)	0.1 uF	R23 (P5/ADC)	Open		
C32 (IF GCA OUT1)	2.2 nF	R24 (IF GCA IN1)	(50 Ω)		
C34 (IF GCA OUT2)	2.2 nF	R25 (IF GCA IN2)	0		
C37 (UHF RF IN1)	2.2 nF	R28 (IF GCA OUT1)	200 Ω		
C39 (UHF RFIN2)	2.2 nF	R30 (IF GCA OUT1)	50 Ω		
C40 (VHI RF IN)	2.2 nF	R31 (IF GCA OUT2)	200 Ω		
C42 (VLO RF IN)	2.2 nF	R34 (IF GCA OUT2)	0		
C47 (MIX OUT)	6 pF	R36 (UHF RF IN1)	(50 Ω)		
C49 (MIX OUT)	2.2 nF	R37 (VHI RF IN)	(50 Ω)		
C51 (RF AGC OUT)	0.15 uF	R38 (VLO RF IN)	(50 Ω)		
C52 (RF AGC BUF)	Open	R42 (MIX OUT)	0		
C56 (IFGCA CTRL)	0.1 µF	R46 (IFGCA CTRL)	0		
C57 (XTAL OUT)	0.01 uF	R47 (XTAL OUT)	5.1 kΩ		
C58 (XTAL OUT)	10 pF	R48 (SDA)	330 Ω		
C59(XTAL)	27 pF	R49 (SCL)	330 Ω		
C60 (XTAL)	27 pF	R50 (AS)	Open		
C61 (VCC)	2.2 nF	VC1 (VLO OSC)	MA2S374		
C62 (SDA)	Open	VC2 (VHI OSC)	MA2S374		
C63 (SCL)	Open	VC3 (UHF OSC)	MA2S372		
C64 (AS)	Open	VC4 (VHI OSC)	MA2S372		
C65 (AS)	22 pF	X1	4-MHz crystal		

(1) IF frequency = 44 MHz Local frequency range : VHF-LOW=101~215 MHz, VHF-HIGH: 221~511 MHz, UHF: 517~908 MHz



APPLICATION INFORMATION (CONTINUED)

Test Circuits





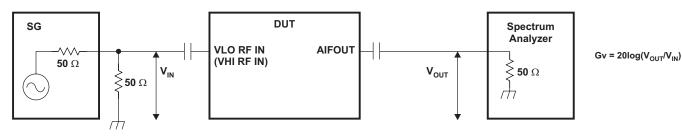


Figure 27. VHF-Conversion Gain Measurement Circuit (at AIFOUT)

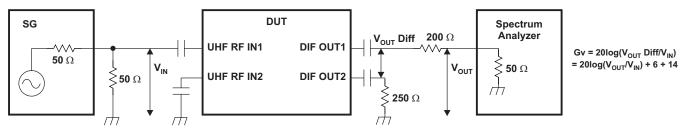
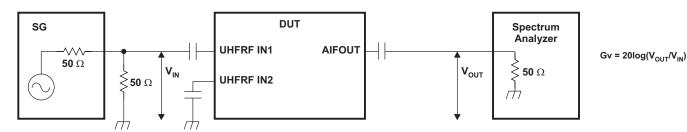


Figure 28. UHF-Conversion Gain-Measurement Circuit (at DIFOUT)





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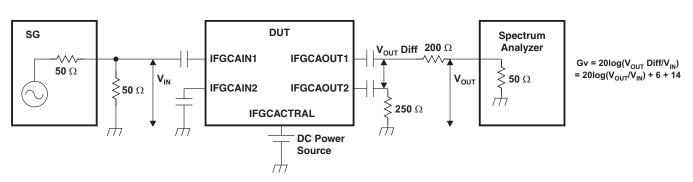


Figure 30. IF GCA Gain Measurement Circuit

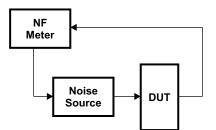


Figure 31. Noise-Figure Measurement Circuit

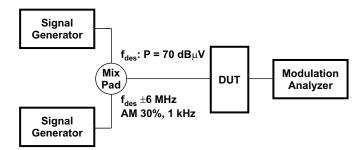


Figure 32. 1% Cross-Modulation Distortion Measurement Circuit

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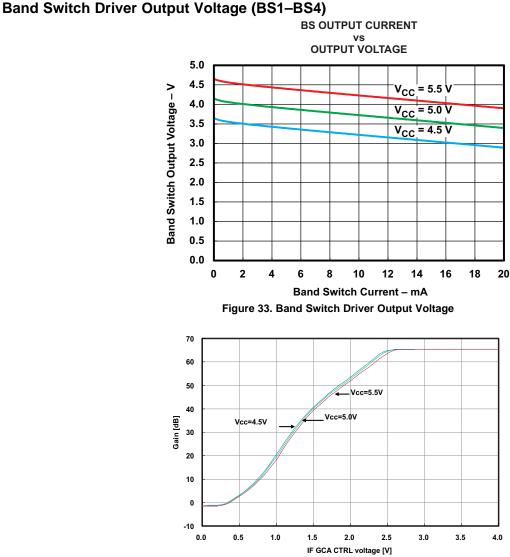


Figure 34. IF GCA Gain vs Control Voltage-1

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TYPICAL CHARACTERISTICS (continued)

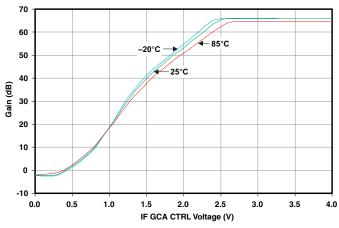


Figure 35. IF GCA Gain vs Control Voltage-2

S-Parameter

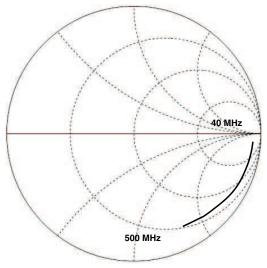


Figure 36. VLO RFIN, VHI RFIN

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TYPICAL CHARACTERISTICS (continued)

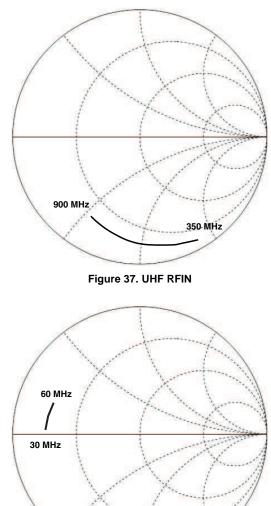
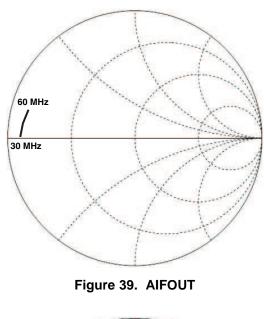


Figure 38. DIFOUT



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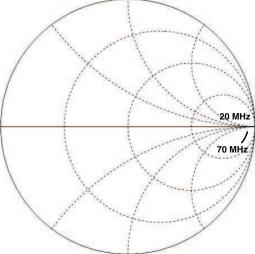


Figure 40. IF GCA IN





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TYPICAL CHARACTERISTICS (continued)

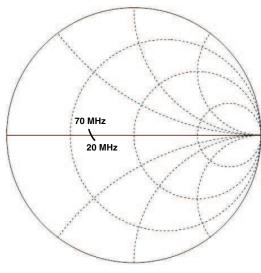


Figure 41. IF GCAOUT



24-Jan-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing			(2)		(3)		(4)	
SN761644DBTR	OBSOLETE	TSSOP	DBT	44		Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-20 to 85	SN761644	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

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the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

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⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

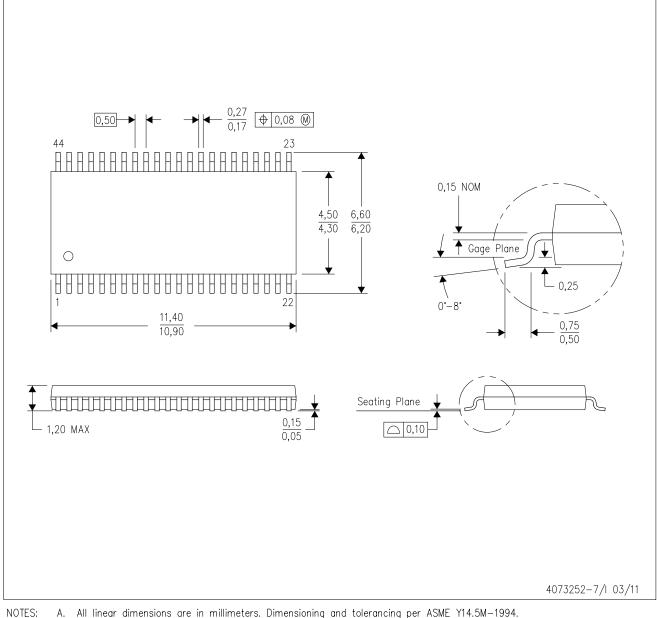
⁽⁴⁾ Only one of markings shown within the brackets will appear on the physical device.

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DBT (R-PDSO-G44)

PLASTIC SMALL OUTLINE



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B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion.



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